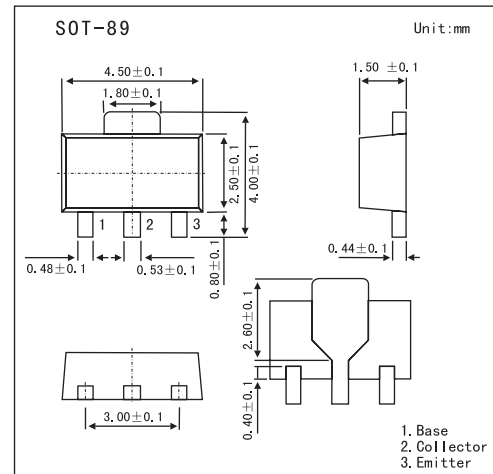


Silicon PNP Epitaxial Planar Type

2SB766,2SB766A

■ Features

- Large collector power dissipation PC
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing



■ Absolute Maximum Ratings Ta = 25°C

Parameter		Symbol	Rating	Unit
Collector-base voltage	2SB766	V _{CB0}	-30	V
	2SB766A		-60	
Collector-emitter voltage	2SB766	V _{CE0}	-25	V
	2SB766A		-50	
Emitter-base voltage		V _{EB0}	-5	V
Collector current		I _C	-1	A
Peak collector current		I _{CP}	-1.5	A
Collector power dissipation		P _C	-1	W
Junction temperature		T _j	150	°C
Storage temperature		T _{stg}	-55 to +150	°C

2SB766,2SB766A■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter		Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base voltage	2SB766	V_{CBO}	$I_C = -10\ \mu\text{A}, I_E = 0$	-30			V
	2SB766A			-60			
Collector-emitter voltage	2SB766	V_{CEO}	$I_C = -2\ \text{mA}, I_B = 0$	-25			V
	2SB766A			-50			
Emitter-base voltage		V_{EBO}	$I_E = -10\ \mu\text{A}, I_C = 0$	-5			V
Collector-base cutoff current		I_{CBO}	$V_{CB} = -20\ \text{V}, I_E = 0$			-0.1	nA
Forward current transfer ratio		h_{FE}	$V_{CE} = -10\ \text{V}, I_C = -500\ \text{mA}$	85		340	
			$V_{CE} = -5\ \text{V}, I_C = -1\ \text{A}$	50			
Collector-emitter saturation voltage		$V_{CE(sat)}$	$I_C = -500\ \text{mA}, I_B = -50\ \text{mA}$		-0.2	-0.4	V
Base-emitter saturation voltage		$V_{BE(sat)}$	$I_C = -500\ \text{mA}, I_B = -50\ \text{mA}$		-0.85	-1.2	V
Transition frequency		f_T	$V_{CB} = -10\ \text{V}, I_E = 50\ \text{mA}, f = 200\ \text{MHz}$		200		MHz
Collector output capacitance		C_{ob}	$V_{CB} = -10\ \text{V}, I_E = 0, f = 1\ \text{MHz}$		20	30	pF

■ h_{FE} Classification

Marking	2SB766(A)/2SB766A(B)		
Rank	Q	R	S
h_{FE}	85~170	120~240	17~340